

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S280	93	((crystallized or recrystallized) near polysilicon) and dram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 15:42
S281	9	((crystallized or recrystallized) near polysilicon).ti,ab,clm. and dram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 15:42
S282	156	((crystallized or recrystallized) near polysilicon).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 15:43
S283	68	((crystallized or recrystallized) near polysilicon near (layer or film)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 15:44
S284	3	((crystallized or recrystallized) near polysilicon near (layer or film)).ti,ab,clm. and capacitor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 15:45
S285	6	((crystallized or recrystallized or crystallize or crystallizing or crystallization) near polysilicon near (layer or film)).ti,ab,clm. and capacitor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 15:46
S286	6	((crystallized or recrystallized or crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization) near polysilicon near (layer or film)).ti,ab,clm. and capacitor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 15:46
S287	53	((crystallized or recrystallized or crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization) near polysilicon near (layer or film)) and capacitor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 15:46

## EAST Search History

S28 8	179	((crystallized or recrystallized or crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization) near polysilicon near (layer or film)) and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 15:48
S28 9	55	((crystallized or recrystallized or crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization) near polysilicon near (layer or film)) and capacitor and dram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 15:53
S29 0	23	((crystallized or recrystallized or crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization) near polysilicon near (layer or film)) and capacitor and (silicide near5 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 15:56
S29 1	388	((crystallized or recrystallized or crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization or crystalline or anneal or annealing or annealed) near2 (silicon or polysilicon or poly) near2 (layer or film)) and capacitor and (silicide near5 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 15:56

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S317	8	S308 and ((polysilicon or silicon) near (layer or film)) near10 (anneal or annealing or annealed) near10 (temperature or celcius or degree) and ((polysilicon or silicon) near (layer or film)) near10 (nm or nanometer or angstrom)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 16:57
S318	4	S308 and ((polysilicon or silicon) near (layer or film)) near10 (anneal or annealing or annealed) near10 (temperature or celcius or degree) and ((polysilicon or silicon) near (layer or film)) near10 (nm or nanometer or angstrom) and (surface near roughness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 17:01
S319	126	((polysilicon or silicon) near (layer or film)) near10 (anneal or annealing or annealed) near10 (temperature or celcius or degree) and ((polysilicon or silicon) near (layer or film)) near10 (nm or nanometer or angstrom) and (surface near roughness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 17:01
S320	42	((polysilicon or silicon) near (layer or film)) near10 (anneal or annealing or annealed) near10 (temperature or celcius or degree) and ((polysilicon or silicon) near (layer or film)) near10 (nm or nanometer or angstrom) and ((surface near roughness) near10 (nm or nanometer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 17:02
S321	1	((polysilicon or silicon) near (layer or film)) near10 (anneal or annealing or annealed) near10 (temperature or celcius or degree) and ((polysilicon or silicon) near (layer or film)) near10 (nm or nanometer or angstrom) and ((surface near roughness) near10 (nm or nanometer)) and capacitor and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 17:02

## EAST Search History

S32 2	11	((polysilicon or silicon) near (layer or film)) near10 (anneal or annealing or annealed) near10 (temperature or celcius or degree) and ((polysilicon or silicon) near (layer or film)) near10 (nm or nanometer or angstrom) and ((surface near roughness)) and capacitor and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 17:04
S32 3	0	(capacitor same electrode same silicide same (surface near roughness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 17:04

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L17	3	(silicide near10 electrode near10 (surface near roughness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 10:47
L18	22	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)) and ((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (anneal or annealing or annealed) near10 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:04
L19	555	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)) and ((polysilicon or polycrystalline or poly) near10 (anneal or annealing or annealed) near10 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:05
L20	113	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)).clm. and ((polysilicon or polycrystalline or poly) near10 (anneal or annealing or annealed) near10 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:05
L21	40	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)).clm. and ((polysilicon or polycrystalline or poly) near10 (anneal or annealing or annealed) near10 temperature).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:06
L22	4	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)).clm. and ((polysilicon or polycrystalline or poly) near10 (anneal or annealing or annealed) near10 temperature).clm. and memory.clm. and capacitor.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:07

## EAST Search History

L23	12	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)).clm. and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 temperature).clm. and memory. clm. and capacitor.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:07
L24	61	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)).clm. and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 temperature).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:07
L25	22	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)).clm. and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 temperature).clm. and capacitor. clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:10
L26	22	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)).clm. and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 (" degree." or temperature)).clm. and capacitor.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:10
L27	61	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)).clm. and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 (" degree." or temperature)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:14



## EAST Search History

L40	3	I39 and ((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)) and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 ("degree." or temperature)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:15
L41	8	I39 and ((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)) and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 ("degree." or temperature))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:16
L42	8	I39 and ((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)) and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 ("degree." or degree or centigrade or celcius or temperature))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:16
L43	61	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)).clm. and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 ("degree." or degree or centigrade or celcius or temperature)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:18
L44	6	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)).clm. and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 ("degree." or degree or centigrade or celcius or temperature) near10 ("1000" or "1100")).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:19

## EAST Search History

L45	6	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)).clm. and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 (".degree." or degree or centigrade or celcius or temperature) near10 ("1000" or "1100" or "1000.quadrature.")).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:19
L46	8	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)).clm. and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 (".degree." or degree or centigrade or celcius or temperature) near10 ("1000" or "1100" or "1000.quadrature."))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:19
L47	33	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)) and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 (".degree." or degree or centigrade or celcius or temperature) near10 ("1000" or "1100" or "1000.quadrature."))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:20
L48	15	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)) and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 (".degree." or degree or centigrade or celcius or temperature) near10 ("1000" or "1100" or "1000.quadrature.")) and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:27
L49	1711	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:27



## EAST Search History

L50	33	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)) and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 (".degree." or degree or centigrade or celcius or temperature) near10 ("1000" or "1100" or "1000.quadrature."))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:31
L51	37	((polysilicon or polycrystalline or poly) near10 (thick or thickness) near10 (angstrom or nm or nanometer)) and ((polysilicon or polycrystalline or poly or silicon) near10 (anneal or annealing or annealed) near10 (".degree." or degree or centigrade or celcius or temperature) near10 ("1000" or "1100" or "1000.quadrature." or "1200" or "1150"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 11:32